

INVERTER (Unbuffer)

The KIC7SU04FU is a high speed C²MOS INVERTER fabricated with silicon gate C²MOS technology.

It achieves high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

The internal circuit is composed of single stages inverter, it can be applied for crystal oscillation.

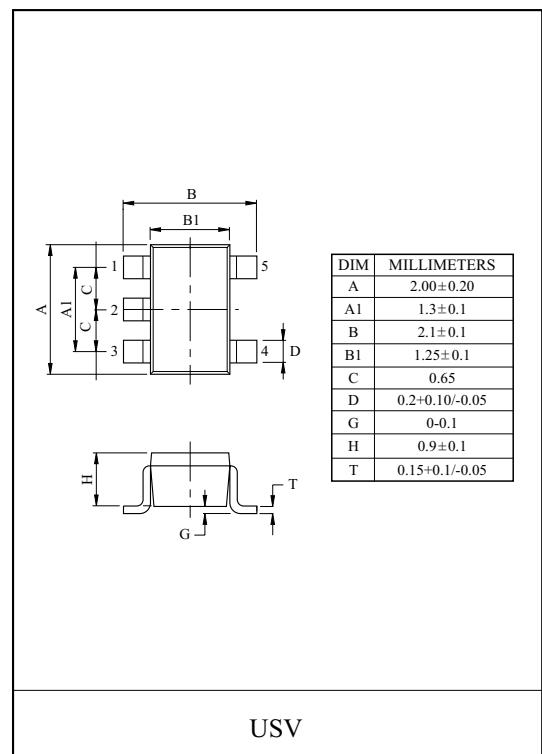
The input is equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

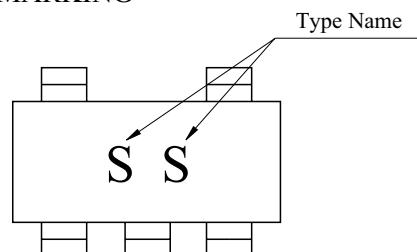
- High Speed : $t_{pd}=7\text{ns}(\text{Typ.})$ at $V_{CC}=5\text{V}$.
- Low Power Dissipation : $I_{CC}=1\mu\text{A}(\text{Max.})$ at $T_a=25^\circ\text{C}$.
- High Noise Immunity : $V_{NIH}=V_{NIL}=28\% V_{CC}(\text{Min.})$.
- Output Drive Capability : 5 LSTTL Loads.
- Symmetrical Output Impedance : $|I_{OH}|=I_{OL}=2\text{mA}(\text{Min.})$
- Balanced Propagation Delays : $t_{pLH}=t_{pHL}$
- Wide Operating Voltage Range : $V_{CC(\text{opr})}=2 \sim 6\text{V}$.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

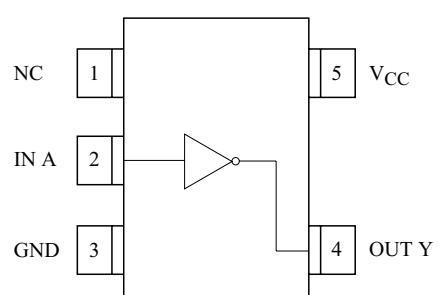
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5 ~ 7	V
DC Input Voltage	V_{IN}	-0.5 ~ $V_{CC}+0.5$	V
DC Output Voltage	V_{OUT}	-0.5 ~ $V_{CC}+0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 12.5	mA
DC V_{CC} /Ground Current	I_{CC}	± 25	mA
Power Dissipation	P_D	200	mW
Storage Temperature	T_{stg}	-65 ~ 150	°C
Lead Temperature (10s)	T_L	260	°C



MARKING

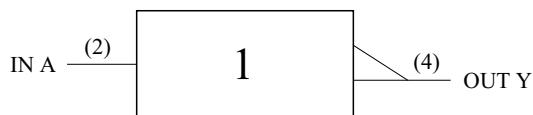


PIN CONNECTION(TOP VIEW)



KIC7SU04FU

LOGIC DIAGRAM



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	2 ~ 6	V
Input Voltage	V _{IN}	0 ~ V _{CC}	V
Output Voltage	V _{OUT}	0 ~ V _{CC}	V
Operating Temperature	T _{opr}	-40 ~ 85	°C

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta=25 °C				Ta=-40 ~ 85 °C		UNIT
			V _{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	V _{IH}	-	2.0	1.7	-	-	1.7	-	V
			4.5	3.6	-	-	3.6	-	
			6.0	4.8	-	-	4.8	-	
Low-Level Input Voltage	V _{IL}	-	2.0	-	-	0.3	-	0.3	V
			4.5	-	-	0.9	-	0.9	
			6.0	-	-	1.2	-	1.2	
High-Level Output Voltage	V _{OH}	V _{IN} =V _{IL}	2.0	1.8	2.0	-	1.8	-	V
			I _{OH} =-20 μA	4.5	4.0	4.5	-	4.0	
				6.0	5.5	5.9	-	5.5	
			I _{OH} =-2mA	4.5	4.18	4.31	-	4.13	
			I _{OH} =-2.6mA	6.0	5.68	5.80	-	5.63	
Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH}	2.0	-	0.0	0.2	-	0.2	V
			I _{OL} =20 μA	4.5	-	0.0	0.2	-	
				6.0	-	0.0	0.5	-	
			I _{OL} =2mA	4.5	-	0.17	0.26	-	
			I _{OL} =2.6mA	6.0	-	0.18	0.26	-	
Input Leakage Current	I _{IN}	V _{IN} =V _{CC} or GND	6.0	-	-	±0.1	-	±1.0	μA
Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND	6.0	-	-	1.0	-	10.0	

KIC7SU04FU

AC ELECTRICAL CHARACTERISTICS (C_L=15pF, Input t_r=t_f=6ns, V_{CC}=5V)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta=25 °C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t _{TLH} t _{THL}	-	-	5	10	ns
Propagation Delay Time	t _{pLH} t _{pHL}	-	-	7	15	ns

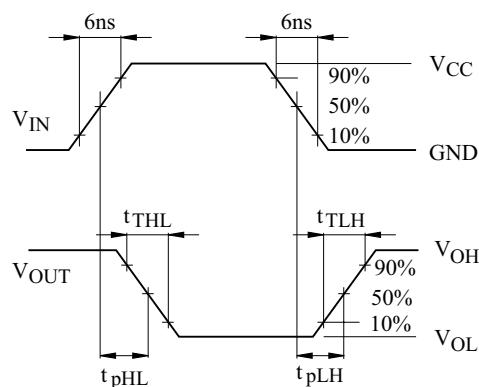
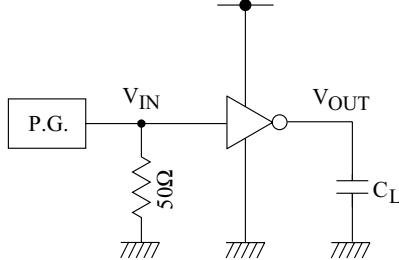
AC ELECTRICAL CHARACTERISTICS (C_L=50pF, Input t_r=t_f=6ns)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta=25 °C			Ta=-40 ~ 85 °C		UNIT
			V _{CC}	MIN.	TYP.	MAX.	MIN.	
Output Transition Time	t _{TLH} t _{THL}	-	2.0	-	50	125	-	155
			4.5	-	14	25	-	31
			6.0	-	12	21	-	26
Propagation Delay Time	t _{pLH} t _{pHL}	-	2.0	-	48	100	-	125
			4.5	-	12	20	-	25
			6.0	-	9	17	-	21
Input Capacitance	C _{IN}	-	-	-	5	10	-	10
Power Dissipation Capacitance	C _{PD}	(Note 1)	-	-	10	-	-	-

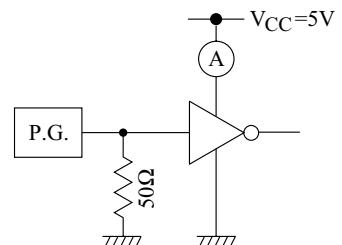
Note 1 : C_{PD} defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit.) Average operating current can be obtained by the equation hereunder.

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

SWITCHING CHARACTERISTICS TEST CIRCUIT



I_{CC(opr)} TEST CIRCUIT



Input waveform is the same as that in case of switching characteristics test.